

Electronic Supplementary Information

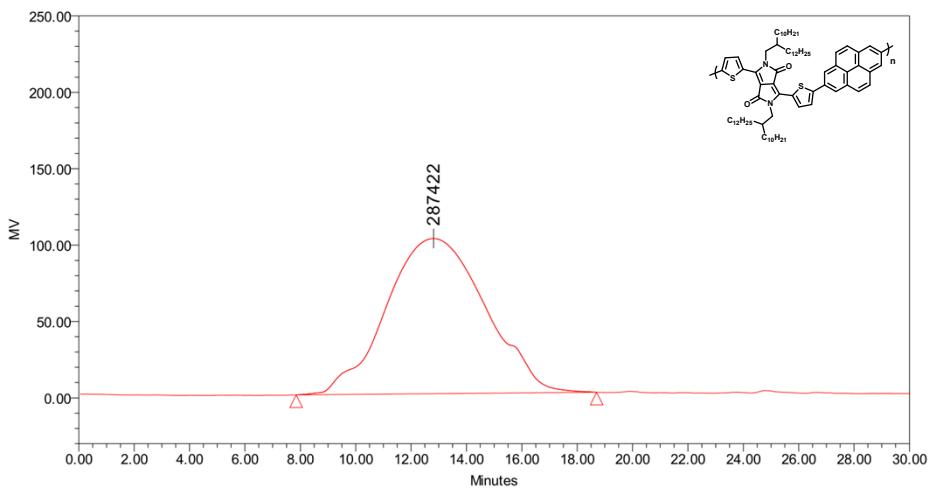
Tunable Light Harvesting Properties of a Highly Crystalline Alternating Terpolymer for High-Performing Solar Cells

Aesun Kim, Dae Hee Lee, Hyun Ah Um, Jicheol Shin, Min Ju Cho and Dong Hoon Choi**

Department of Chemistry, Research Institute for Natural Sciences, Korea University 5 Anam-dong, Sungbuk-gu, Seoul 136-701, Republic of Korea

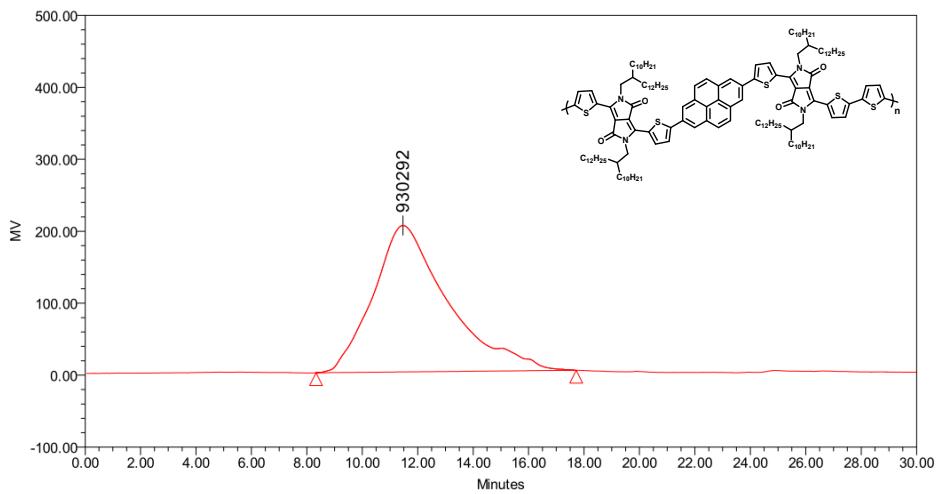
KEYWORDS conjugated copolymer, terpolymer, thin film transistors, organic photovoltaics

Gel Permeation Chromatograms



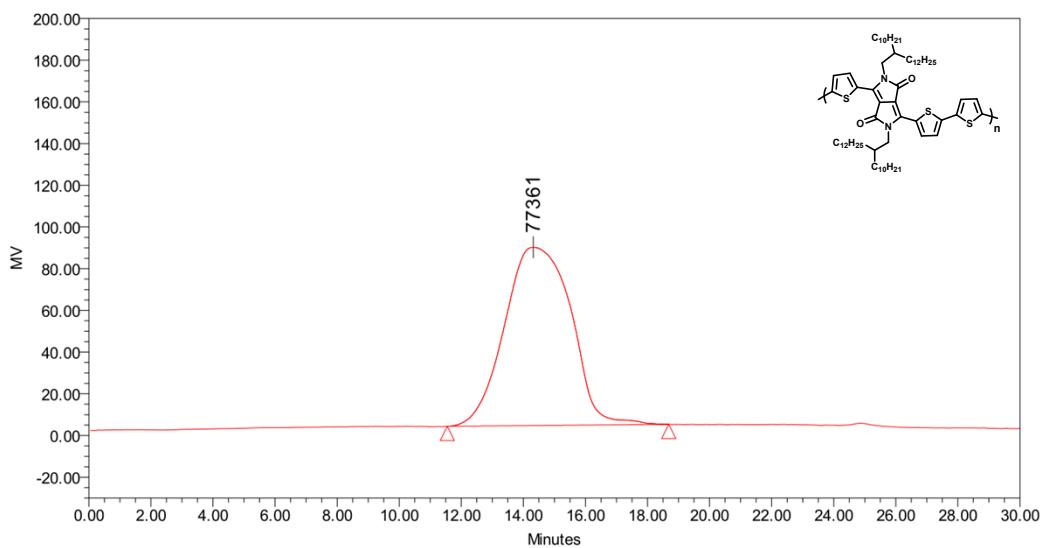
M_n (Da)	M_w (Da)	M_p (Da)	M_z (Da)	Polydispersity	% Area
94798	626553	287422	2586645	6.609313	100.00

Fig. S1 GPC chromatogram of PDPPPPy.



M_n (Da)	M_w (Da)	M_p (Da)	M_z (Da)	Polydispersity	% Area
197790	1095020	930292	2557106	5.536283	100.00

Fig. S2 GPC chromatogram of PDPPPPyT.



M_n (Da)	M_w (Da)	M_p (Da)	M_z (Da)	Polydispersity	% Area
46558	90056	77361	155962	1.934260	100.00

Fig. S3 GPC chromatogram of PDPPT.

Thermal analysis

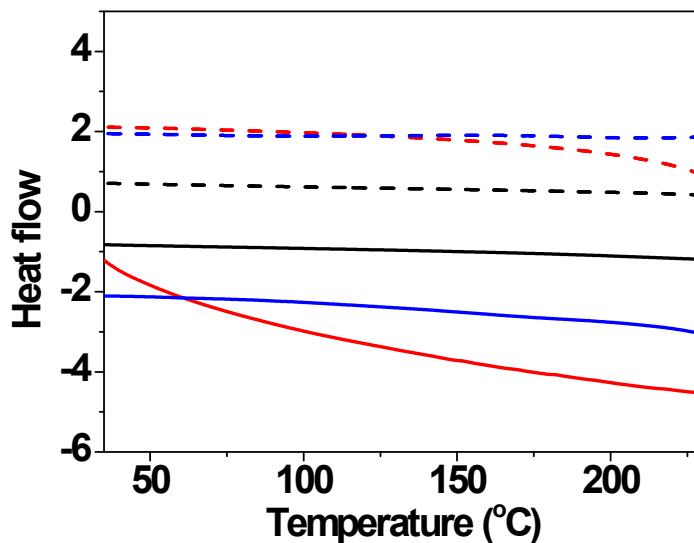


Fig. S4 DSC thermograms of PDPPPy (black), PDPPPyT (red), and PDPPT (blue). Heating cycle (solid line) and cooling cycle (dashed line).

GI-XRD Data

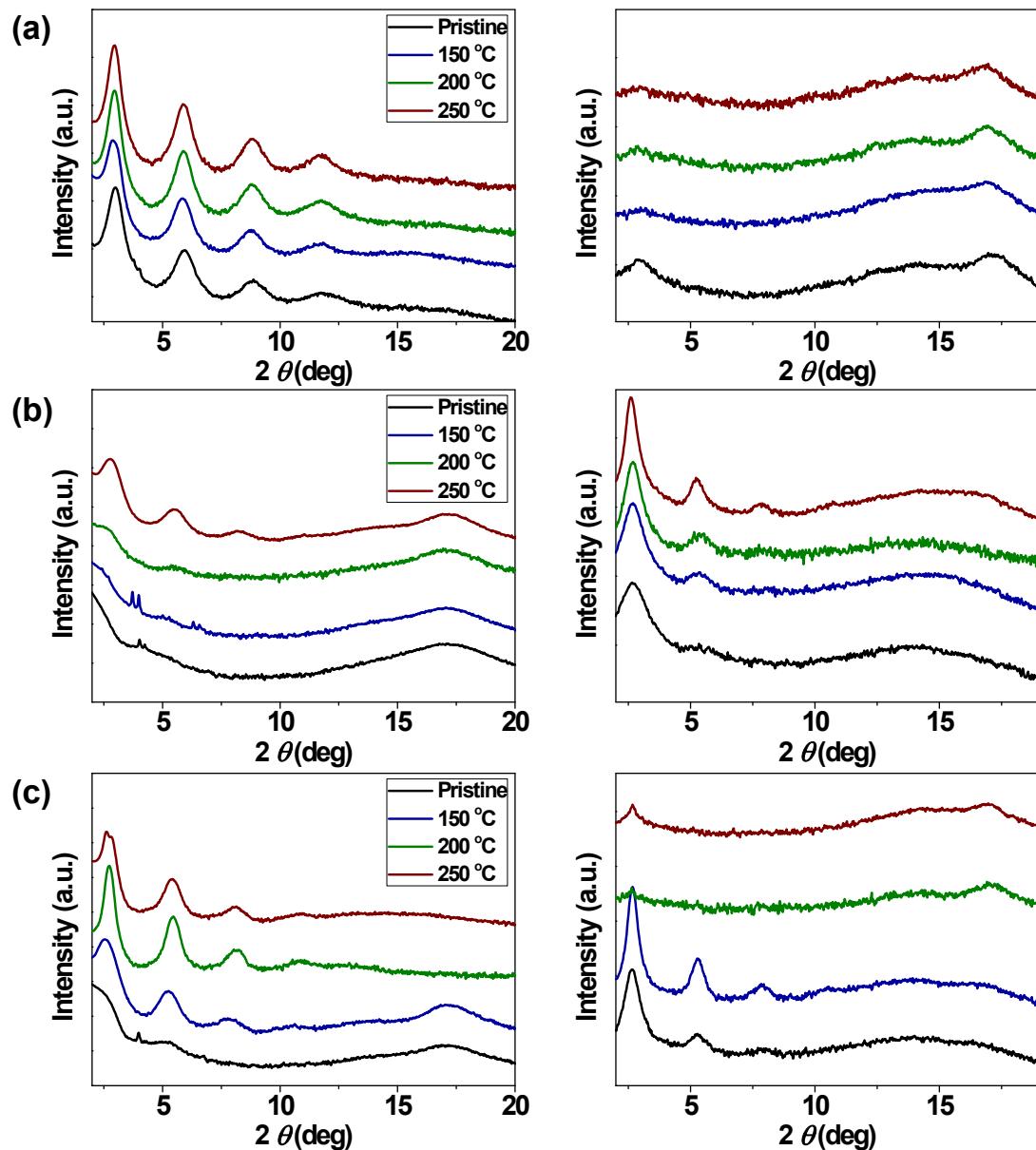


Fig. S5 Out-of-plane and in-plane profiles of XRD patterns. Sample: thermally annealed films of (a) PDPPPPy, (b) PDPPPPyT and (c) PDPPT. Out-of-plane (left side) and in-plane (right side).

Table S1 Crystallographic parameters calculated from the GI-XRD profiles of PDPPP_y.

Crystallographic parameters	Annealing Temperature				
	Pristine	150 °C	200 °C	250 °C	
Out-of-plane (100)	q_z (\AA^{-1})	0.2808	0.2686	0.2754	0.2764
	d -spacing (\AA)	21.43	22.29	21.73	21.76
	FWHM (\AA^{-1})	0.0351	0.0467	0.0315	0.0309
In-plane (100)	q_z (\AA^{-1})	0.2810	0.2926	0.2829	0.2887
	d -spacing (\AA)	22.36	20.14	22.21	21.76
	FWHM (\AA^{-1})	-	-	-	-

Table S2 Crystallographic parameters calculated from the GI-XRD profiles of PDPPPyT.

Crystallographic parameters	Annealing Temperature				
	Pristine	150 °C	200 °C	250 °C	
Out-of-plane (100)	q_z (\AA^{-1})	-	-	-	0.2585
	d -spacing (\AA)	-	-	-	23.41
	FWHM (\AA^{-1})	-	-	-	0.0740
In-plane (100)	q_z (\AA^{-1})	0.2596	0.2635	0.2635	0.2557
	d -spacing (\AA)	24.20	23.85	23.85	24.57
	FWHM (\AA^{-1})	0.1022	0.0712	0.0507	0.0338

Table S3 Crystallographic parameters calculated from the GI-XRD profiles of PDPPT.

Crystallographic parameters	Annealing Temperature				
	Pristine	150 °C	200 °C	250 °C	
Out-of-plane (100)	q_z (\AA^{-1})	-	0.2347	0.2560	0.2414
	d -spacing (\AA)	-	25.49	23.46	25.49
	FWHM (\AA^{-1})	-	0.0619	0.0245	0.0407
In-plane (100)	q_z (\AA^{-1})	0.2635	0.2616	0.2577	0.2616
	d -spacing (\AA)	23.39	24.02	24.39	24.02
	FWHM (\AA^{-1})	0.0437	0.0245	-	-

Output curves of the TFTs

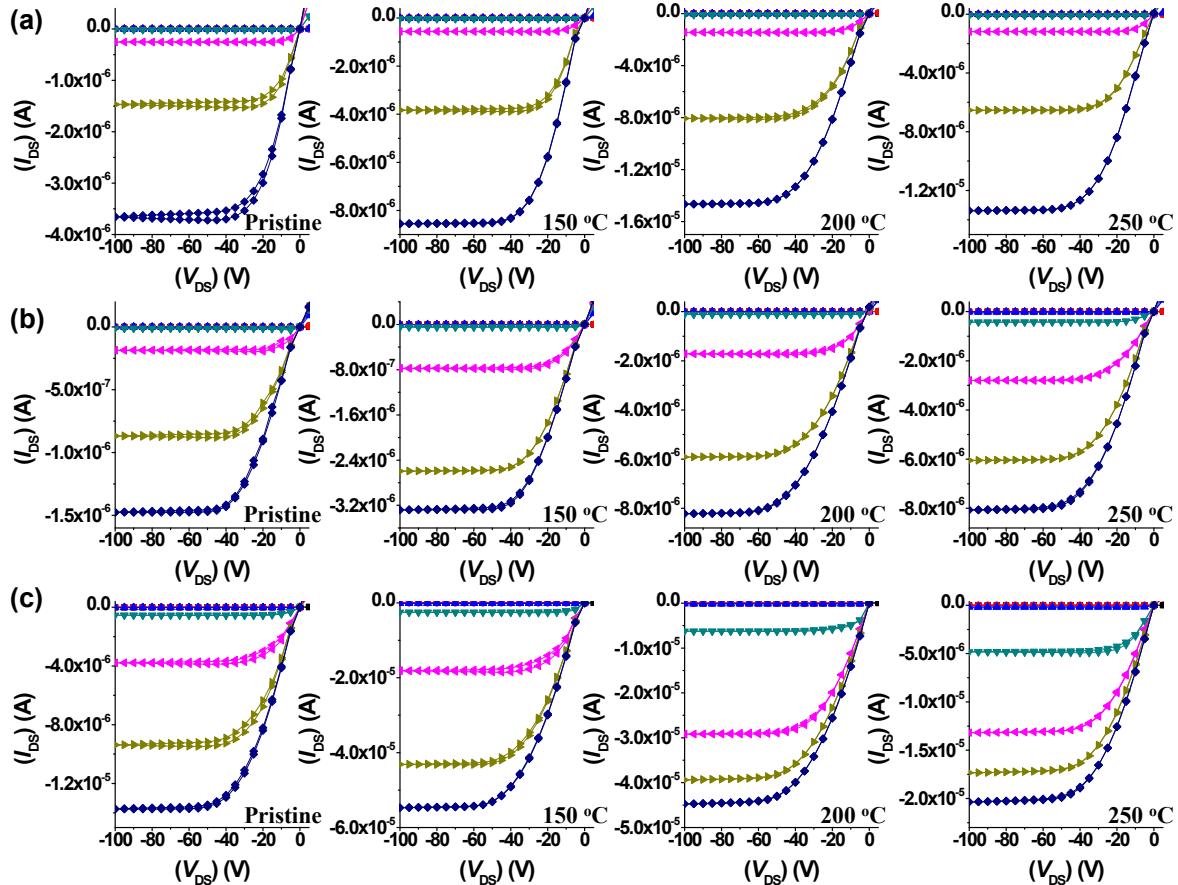


Fig. S6 Output curves of (a) PDPPPPy, (b) PDPPPPyT, and (c) PDPPT TFTs. The range of the output curves is -40 to 20 V and $V_{DS} = -100$ V.

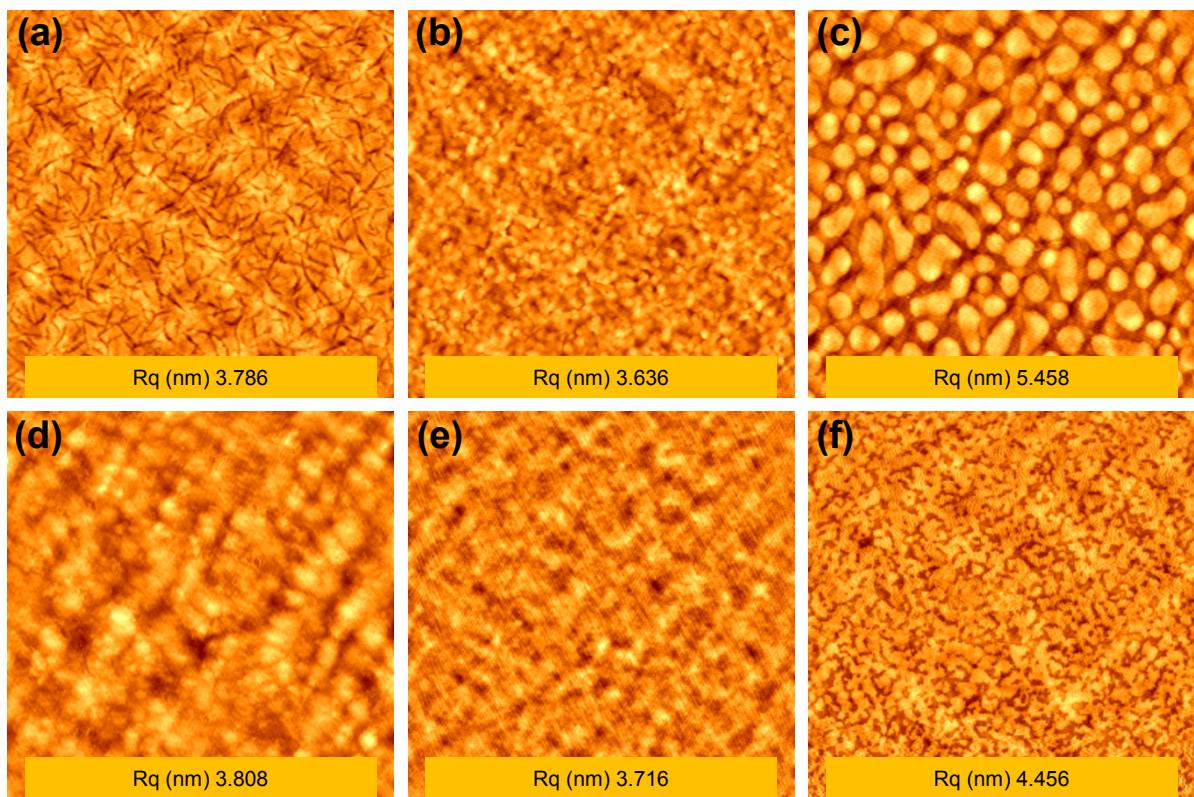


Fig. S7. AFM images (size: 10 μm X 10 μm) of photoactive layers. PDPPP_y (a, d), PDPPP_{yT} (b, e), and PDPPT (c, f). (a, b, c): the images obtained without DIO and (d, e, f): the images obtained with 3 vol% DIO.

The surface morphology of the active PSC layer was measured by AFM for better understanding the basis for the improved performance observed by adding DIO additives. As shown in Fig. S7, the surface morphology was observed to be different by adding 3 vol% DIO into the photoactive layers.